

(12) UK Patent Application (19) GB (11) 2 345 286 (13) A

(43) Date of A Publication 05.07.2000

(21) Application No 9929650.1

(22) Date of Filing 15.12.1999

(30) Priority Data

(31) 99063793 (32) 31.12.1998 (33) KR

(71) Applicant(s)

Hyundai Electronics Industries Co., Ltd.
(Incorporated in the Republic of Korea)
San 138-1, Ami-ri, Bubal-eub, Ich'on, Kyoungki-do,
Republic of Korea

(72) Inventor(s)

Jaee Chang Jung
Keun Kyu Kong
Min Ho Jung
Gaun Su Lee
Ki Ho Baik

(74) Agent and/or Address for Service

Maguire Boss
5 Crown Street, ST IVES, Cambridgeshire, PE27 5EB,
United Kingdom

(51) INT CL⁷

C07C 69/602, C08F 22/14

(52) UK CL (Edition R)

C2C CAA CCJ C20Y C200 C30Y C366 C368 C37X C638
C815
C3P PDY
U1S S1409

(56) Documents Cited

US 5777068 A US 4329419 A

(58) Field of Search

UK CL (Edition R) C2C CCH, C3P PDY
INT CL⁷ C07C 69/602, C08F 22/14

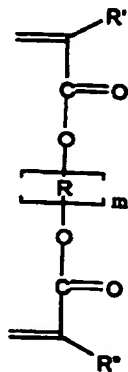
ONLINE: CAS-ONLINE, EPODOC, JAPIO, WPI

(54) Abstract Title

Cross-linking monomers for photoresist, and process for preparing photoresist polymers using the same

(57) A cross-linking monomer represented by the following Chemical Formula 1, process for preparing a photoresist polymer using the same, and said photoresist polymer:

<Chemical Formula 1>



wherein, R' and R'' individually represent hydrogen or methyl; m represents a number of 1 to 10; and R is selected from the group consisting of straight or branched C₁₋₁₀ alkyl, straight or branched C₁₋₁₀ ester, straight or branched C₁₋₁₀ ketone, straight or branched C₁₋₁₀ carboxylic acid, straight or branched C₁₋₁₀ acetal, straight or branched C₁₋₁₀ alkyl including at least one hydroxyl group, straight or branched C₁₋₁₀ ester including at least one hydroxyl group, straight or branched C₁₋₁₀ ketone including at least one hydroxyl group, straight or branched C₁₋₁₀ carboxylic acid including at least one hydroxyl group, and straight or branched C₁₋₁₀ acetal including at least one hydroxyl group.

GB 2 345 286 A

1/2

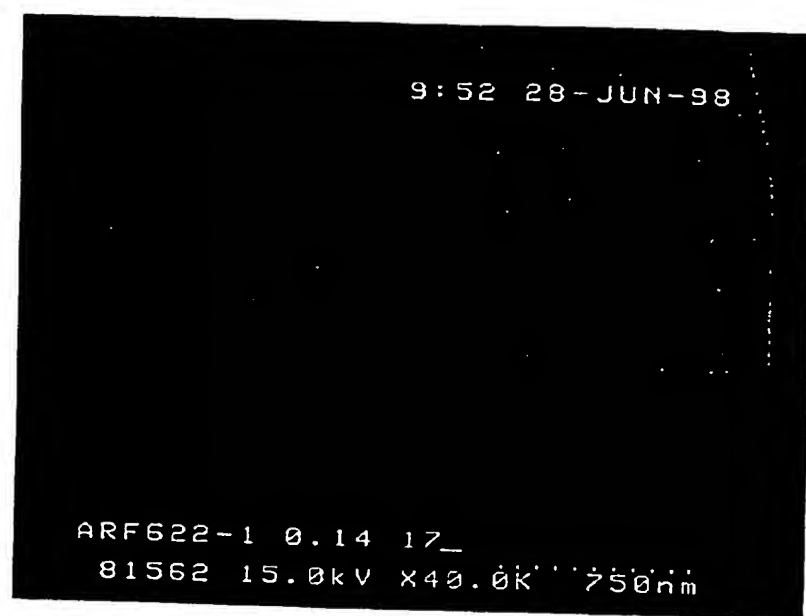


Fig.1

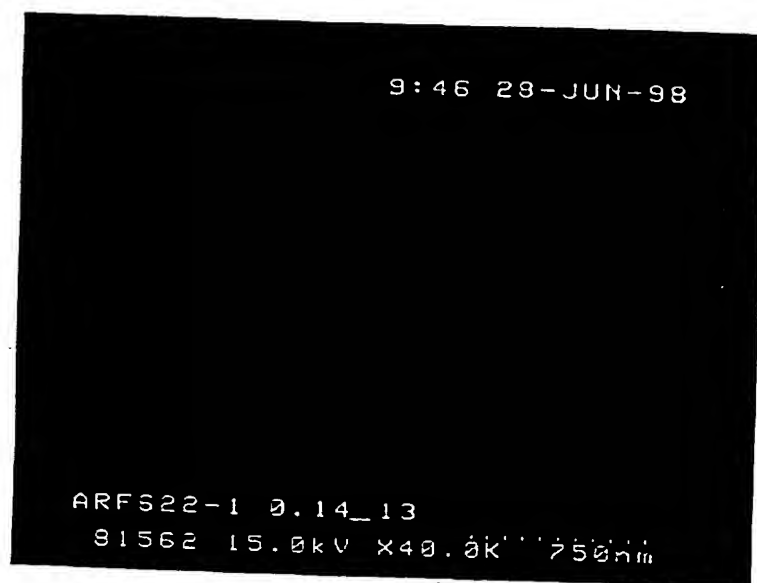


Fig.2

CROSS-LINKING MONOMERS FOR PHOTORESIST, AND PROCESS FOR PREPARING PHOTORESIST POLYMERS USING THE SAME

Field of the Invention

5 The present invention relates to cross-linking monomers for photoresist polymers, and processes for preparing photoresist polymers using the same. More specifically, it relates to cross-linking monomers for photoresist polymers which can noticeably improve the polymerization ratio of photoresist copolymers, and a process for preparing photoresist copolymers using the same.

10

Background of the Invention

Recently, chemical amplification-type DUV (deep ultra violet) photoresists have proven to be useful to achieve high sensitivity in processes for preparing micro-circuits in the manufacture of semiconductors. These photoresists are prepared by
15 blending a photoacid generator with polymer matrix macromolecules having acid labile structures.

According to the reaction mechanism of such a photoresist, the photoacid generator generates acid when it is irradiated by the light source, and the main chain or branched chain of the polymer matrix in the exposed portion is reacted with the
20 generated acid to be decomposed or cross-linked, so that the polarity of the polymer is considerably altered. This alteration of polarity results in a solubility difference in the developing solution between the exposed area and the unexposed area, thereby forming a positive or negative image of a mask on the substrate.

In some photoresists, functional groups on the main chain or branched chain
25 of one polymer are cross-linked with the main chain or branched chain of another polymer in the matrix. A cross-linker is therefore added to the photoresist to promote cross-linking between the polymers.

However, a cross-linking monomer can also be used to promote bonding between the monomers constituting a photoresist polymer, thereby enhancing the yield of the photoresist polymer. For example, when 20 g of monomer is used in the polymerization reaction without using a cross-linker, about 4.8 g of a polymer having molecular weight of about 6,000 is obtained (yield: 24%). When the amount of the monomer is increased to 40 g, the amount of the polymer obtained is only about 6 g (i.e., the yield is abruptly lowered to about 15%). Thus, in order to prepare photoresist polymer in a large scale, it is desirable to use a cross-linking monomer to increase the yield and make production of the photoresist polymer commercially reasonable.

Summary of the Invention

The object of the present invention is to provide a cross-linking monomer for a photoresist polymer which can noticeably improve the polymerization yield of the photoresist polymer.

Another object of the present invention is to provide a process for preparing a photoresist polymer using said cross-linking monomer, and a photoresist polymer prepared therefrom.

Another object of the present invention is to provide photoresist compositions prepared by using polymers formed from the cross-linking monomer described above.

Still another object of the present invention is to provide a semiconductor element manufactured by using the photoresist composition described above.

Brief Description of the Drawings

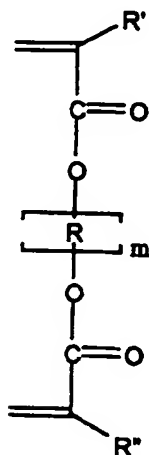
Fig. 1 shows a photoresist pattern obtained from Example 3.

Fig. 2 shows a photoresist pattern obtained from Example 4.

Detailed Description of the Invention

To achieve the object described above, the present invention provides a cross-linking monomer represented by the following Chemical Formula 1:

<Chemical Formula 1>



wherein, R' and R'' individually represent hydrogen or methyl; m represents a number from 1 to 10; and R is selected from the group consisting of straight or branched C₁₋₁₀ alkyl, straight or branched C₁₋₁₀ ester, straight or branched C₁₋₁₀ ketone, straight or branched C₁₋₁₀ carboxylic acid, straight or branched C₁₋₁₀ acetal, straight or branched C₁₋₁₀ alkyl including at least one hydroxyl group, straight or branched C₁₋₁₀ ester including at least one hydroxyl group, straight or branched C₁₋₁₀ ketone including at least one hydroxyl group, straight or branched C₁₋₁₀ carboxylic acid including at least one hydroxyl group, and straight or branched C₁₋₁₀ acetal including at least one hydroxyl group.

To achieve another object of the present invention, a process is provided for preparing a photoresist copolymer, which comprises the steps of (a) dissolving two or more photoresist comonomers and a cross-linking monomer of Chemical Formula 1 in an organic solvent, and (b) adding a polymerization initiator or a polymerization

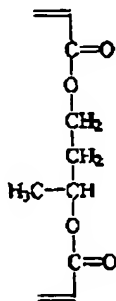
catalyst to the resultant solution to induce polymerization.

The inventors have performed intensive studies to achieve the objects of the invention described above, and have found that a compound represented by Chemical Formula 1 improves the polymerization yield of polymers by making the photoresist polymers cross-link to one another. The cross-linking monomer of the present invention is particularly effective to improve the polymerization yield of copolymers having an alicyclic olefin main chain.

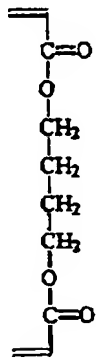
The compound represented by Chemical Formula 1 has two double bonds, and each double bond combines with the other photoresist monomers to form cross-linking, thereby enhancing the polymerization yield of the photoresist polymer.

Preferably, the cross-linking monomer of Chemical Formula 1 is 1,3-butanediol diacrylate represented by Chemical Formula 2 or 1,4-butanediol diacrylate represented by Chemical Formula 3.

<Chemical Formula 2>



<Chemical Formula 3>

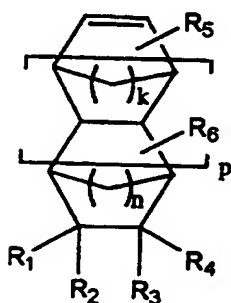


Preparation of photoresist polymers

The process for photoresist polymerization according to the present invention can be performed by adding a cross-linking monomer of Chemical Formula 1 to other photoresist monomers in the process for synthesizing a conventional photoresist copolymer.

For example, in the case of preparing a photoresist copolymer from alicyclic olefin derivatives, for example, as represented by the following Chemical Formula 4, polymerization is performed by dissolving two or more compounds represented by Chemical Formula 4 and a cross-linking monomer of Chemical Formula 1 in organic solvent, and adding a radical initiator or a metal catalyst to the resultant solution to induce polymerization:

<Chemical Formula 4>



wherein, k and n individually represent the number 1 or 2; p represents a number from 0 to 5, R₅ and R₆ individually represent hydrogen or methyl, R₁, R₂, R₃, and R₄ individually represent hydrogen, straight or branched C₁₋₁₀ alkyl, straight or branched C₁₋₁₀ ester, straight or branched C₁₋₁₀ ketone, straight or branched C₁₋₁₀ carboxylic acid, straight or branched C₁₋₁₀ acetal, straight or branched C₁₋₁₀ alkyl including at least one hydroxyl group, straight or branched C₁₋₁₀ ester including at least one hydroxyl group, straight or branched C₁₋₁₀ ketone including at least one hydroxyl group, straight or branched C₁₋₁₀ carboxylic acid including at least one hydroxyl group, and straight or branched C₁₋₁₀ acetal

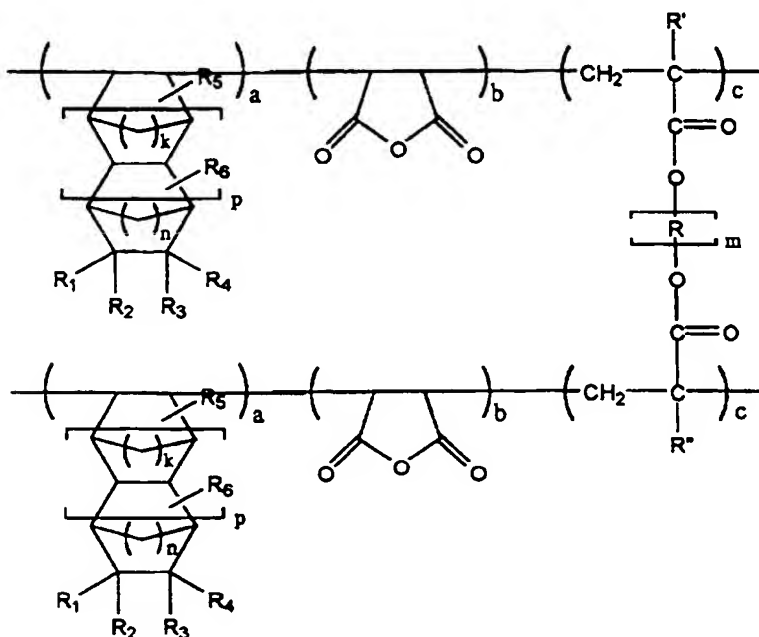
including at least one hydroxyl group.

It is desirable to carry out the polymerization reaction at a temperature between 60°C and 130°C and at a pressure between 0.0001 and 5 atm under nitrogen or argon atmosphere.

5 Bulk polymerization or solution polymerization may be employed as a polymerization process, and cyclohexanone, methyl ethyl ketone, benzene, toluene, dioxane, tetrahydrofuran, propylene glycol methyl ether acetate and/or dimethylformamide, or mixtures thereof, may be used as a polymerization solvent. As a polymerization initiator, benzoyl peroxide, 2,2'-azobisisobutyronitrile (AIBN),
10 acetyl peroxide, lauryl peroxide, tert-butyl peracetate, tert-butyl hydroperoxide, di-tert-butyl peroxide, or the like may be used.

A desirable photoresist polymer prepared by using the polymerization process of the present invention is represented by following Chemical Formula 5:

<Chemical Formula 5>



wherein, k and n individually represent the number 1 or 2; m represents a

number from 1 to 10; p represents a number from 0 to 5; R', R'', R₅ and R₆ individually represent hydrogen or methyl; R is selected from the group consisting of straight or branched C₁₋₁₀ alkyl, straight or branched C₁₋₁₀ ester, straight or branched C₁₋₁₀ ketone, straight or branched C₁₋₁₀ carboxylic acid, straight or branched C₁₋₁₀ acetal, straight or branched C₁₋₁₀ alkyl including at least one hydroxyl group, straight or branched C₁₋₁₀ ester including at least one hydroxyl group, straight or branched C₁₋₁₀ ketone including at least one hydroxyl group, straight or branched C₁₋₁₀ carboxylic acid including at least one hydroxyl group, and straight or branched C₁₋₁₀ acetal including at least one hydroxyl group; R₁, R₂, R₃ and R₄ are individually selected from the group consisting of hydrogen, straight or branched C₁₋₁₀ alkyl, straight or branched C₁₋₁₀ ester, straight or branched C₁₋₁₀ ketone, straight or branched C₁₋₁₀ carboxylic acid, straight or branched C₁₋₁₀ acetal, straight or branched C₁₋₁₀ alkyl including at least one hydroxyl group, straight or branched C₁₋₁₀ ester including at least one hydroxyl group, straight or branched C₁₋₁₀ ketone including at least one hydroxyl group, straight or branched C₁₋₁₀ carboxylic acid including at least one hydroxyl group, and straight or branched C₁₋₁₀ acetal including at least one hydroxyl group; and the ratio a : b : c is preferably 1-50 mol% : 10-50 mol% : 0.1-20 mol%.

The molecular weight of the photoresist polymer represented by Chemical Formula 5 is preferably 3,000 to 100,000.

The photoresist polymer according to the present invention shows no significant difference in photolithographic performance from a polymer formed without a cross-linking monomer. However, when the cross-linking monomer of the present invention is employed, the polymerization yield is noticeably increased.

For example, when 20 g of comonomer is employed in the polymerization without using a cross-linking monomer, about 4.8 g of a polymer having molecular weight of about 6,000 is obtained (yield: 24%). When the amount of the comonomer

is increased to 40 g, the amount of the polymer obtained is only about 6 g (i.e., the yield is abruptly lowered to about 15% when larger quantities of reactants are used). Thus, merely increasing the quantity of reactants is not a suitable method for producing the copolymer on a large scale.

5 On the other hand, in the case of performing the same polymerization process using a cross-linking monomer according to the present invention, when 20 g of comonomer is used in the polymerization, about 7 g of the polymer having molecular weight of about 12,000 is obtained (yield: 35%); and, when the amount of the comonomer is increased to 40 g, the amount of the polymer obtained was about 14 g
10 (yield: 35% i.e., no substantial change in the polymerization yield). The molecular weight of the obtained photoresist copolymer was 12,000, and the poly dispersity was about 2.0.

As shown above, higher yields can be obtained when the polymerization is performed using the cross-linking monomer of the present invention, thereby
15 allowing the resultant photoresist polymer to be prepared on a large scale.

Preparation of photoresist compositions

A photoresist composition can be prepared according to the present invention by mixing a photoresist polymer of the present invention with an organic solvent.
20 Cyclohexanone, methyl 3-methoxypropionate, ethyl 3-ethoxypropionate, propylene glycol methyl ether acetate, 2-methoxyethyl acetate, 2-heptanone, isobutyl methyl ketone, or the other conventional organic solvents may be used.

Optionally, a small amount of a photoacid generator may also be added to the photoresist composition. Examples of suitable photoacid generators, including
25 sulfide or onium type photoacid generators, such as diphenyl iodide hexafluorophosphate, diphenyl iodide hexafluoroarsenate, diphenyl iodide hexafluoroantimonate, diphenyl p-methoxyphenyl triflate, diphenyl p-toluenyl

triflate, diphenyl p-isobutylphenyl triflate, diphenyl p-tert-butylphenyl triflate, triphenylsulfonium hexafluorophosphate, triphenylsulfonium hexafluoroarsenate, triphenylsulfonium hexafluoroantimonate, triphenylsulfonium triflate, dibutyl-naphthylsulfonium triflate, and the like.

5

Formation of a photoresist pattern

A photoresist composition prepared according to the present invention may be spin-coated on a silicon wafer to form a thin photoresist film thereon, which is then "soft-baked" in an oven or on a hot plate at 70°C to 200°C, preferably at 80°C to 150°C, for 1 to 5 minutes, and then exposed to patterned light by using a deep ultraviolet exposer or an excimer laser exposer. As the light source, ArF, KrF, E-beam, X-ray, EUV (extremely ultraviolet), DUV (deep ultraviolet) or the like may also be used, and the energy of light exposure is preferably from 1 to 100 mJ/cm².

Then, the thin photoresist film is "post-baked" at 10° to 200°C, preferably at 100°C to 200°C, and the resultant material is impregnated with 2.38wt% or 2.5wt% aqueous TMAH developing solution for a predetermined time, preferably for 40 seconds, to obtain an ultramicro pattern.

A semiconductor element with high integrity can be manufactured by using the photoresist pattern according to the present invention.

The above description discloses only certain embodiments related to processes for preparing a photoresist copolymer or a photoresist composition by using a cross-linking monomer. It should be understood that the present invention is not restricted to these examples, but includes using the cross-linking monomer of the present invention in any process for producing a conventional photoresist copolymer or photoresist composition.

Detailed Description of Preferred Embodiment

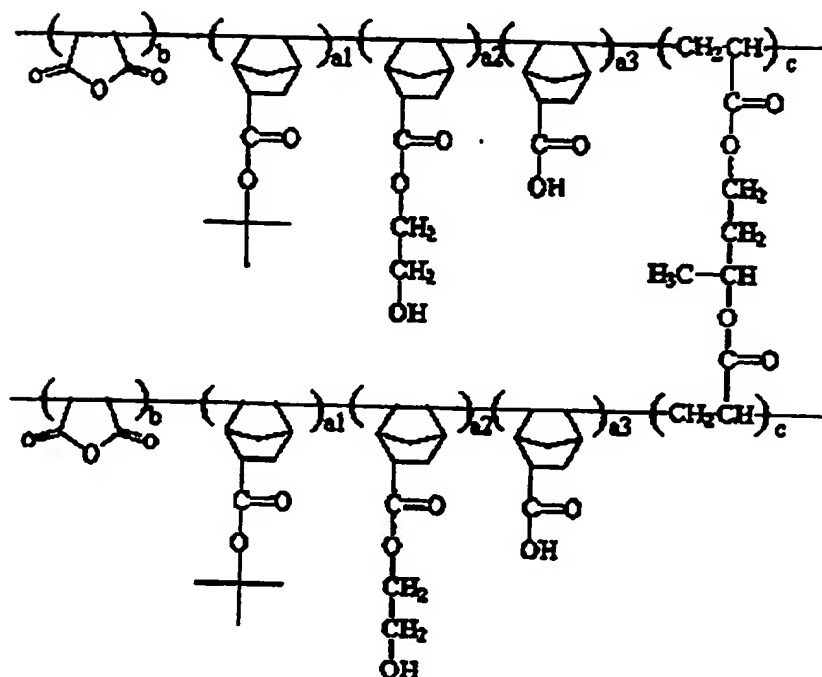
The invention is described in more detail by referring to the examples below, but it should be noted that the present invention is not restricted to these examples.

5 Example 1 : Synthesis of poly(maleic anhydride / 2-hydroxyethyl 5-norbornene-2-carboxylate / tert-butyl 5-norbornene-2-carboxylate / 5-norbornene-2-carboxylic acid / 1,3-butanediol diacrylate)

10 First, (i) 2-hydroxyethyl 5-norbornene-2-carboxylate (0.1 mole), (ii) tert-butyl 5-norbornene-2-carboxylate (0.85 mole), (iii) 5-norbornene-2-carboxylic acid (0.05 mole), (iv) 1,3-butanediol diacrylate (0.1 mole), which is a cross-linking monomer within the scope of Chemical Formula 2, and (v) maleic anhydride (1.0 mole) are dissolved in tetrahydrofuran.

15 2,2'-azobisisobutyronitrile (AIBN) (6.16g) is added to the resultant solution as a polymerization initiator, and the mixture is reacted at 67°C for 10 hours under an atmosphere of nitrogen or argon. The polymer thus obtained is precipitated from ethyl ether or hexane, and dried to obtain poly(maleic anhydride / 2-hydroxyethyl 5-norbornene-2-carboxylate / tert-butyl 5-norbornene-2-carboxylate / 5-norbornene-2-carboxylic acid / 1,3-butanediol diacrylate) of following Chemical Formula 6 (yield : 35 %):

<Chemical Formula 6>

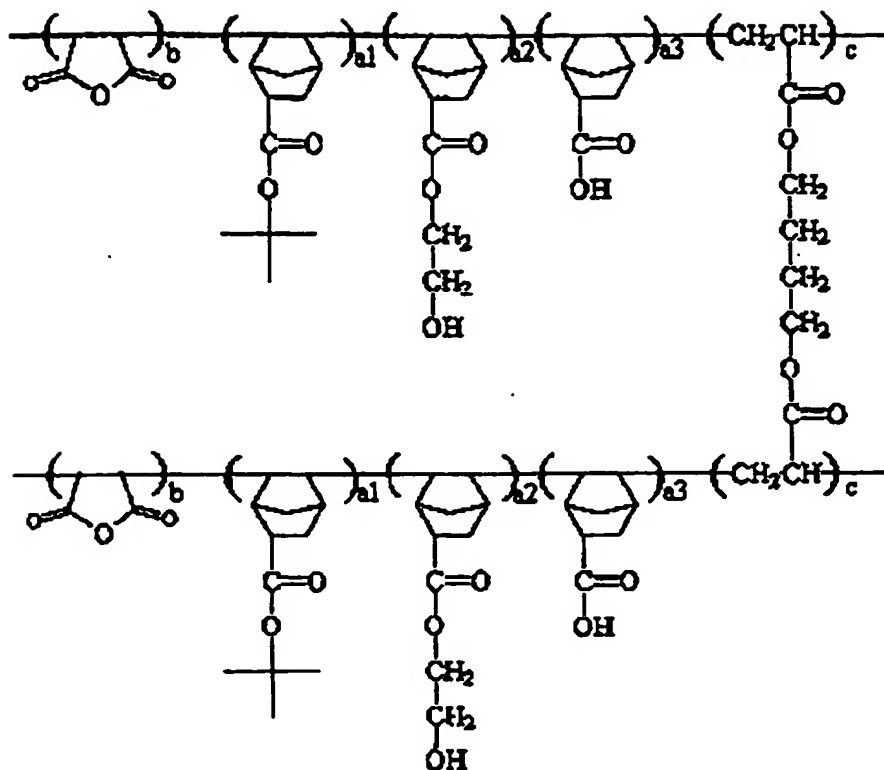


The molar ratio $a_1 : a_2 : a_3 : b : c$ is 0.405 : 0.048 : 0.024 : 0.476 : 0.047.

5 Example 2 : Synthesis of poly(maleic anhydride / 2-hydroxyethyl 5-norbornene-2-carboxylate / tert-butyl 5-norbornene-2-carboxylate / 5-norbornene-2-carboxylic acid / 1,4-butanediol diacrylate)

10 The procedure of Example 1 is repeated but using 1,4-butanediol diacrylate instead of 1,3-butanediol diacrylate, to obtain poly (maleic anhydride / 2-hydroxyethyl 5-norbornene-2-carboxylate / tert-butyl 5-norbornene-2-carboxylate / 5-norbornene-2-carboxylic acid / 1,4-butanediol diacrylate) of following Chemical Formula 7:

<Chemical Formula 7>



The molar ratio $a_1 : a_2 : a_3 : b : c$ is 0.405 : 0.048 : 0.024 : 0.476 : 0.047.

Example 3

5 After dissolving the photoresist polymer of Chemical Formula 6, obtained from Example 1 (3.57 g), in ethyl 3-ethoxypropionate (25 g), triphenylsulfonium triflate (0.02 g) is added as a photoacid generator, and the resultant mixture is filtered through a 0.10 μ m filter to prepare a photoresist composition.

10 The photoresist composition thus prepared is spin-coated on a silicon wafer, and soft-baked at 110°C for 90 seconds. Then, after irradiating with light having exposure energy of 0.1 to 40 mJ/cm² using an ArF laser exposers, the wafer is post-baked again at 110°C for 90 seconds. When the post-baking is completed, it was developed in 2.38wt% aqueous TMAH solution for 40 seconds, to obtain 0.14 μ m

L/S pattern (Fig. 1).

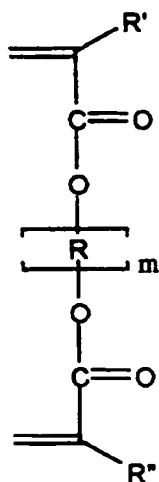
Example 4

5 The procedure according to Example 3 is repeated but using the photoresist polymer of Chemical Formula 7 obtained from Example 2, instead of the polymer obtained from Example 1, to form a photoresist pattern. An ultramicro pattern of 0.14 μ m L/S was obtained (Fig. 2).

What is claimed is:

1. A cross-linking monomer for a photoresist polymer represented by following Chemical Formula 1:

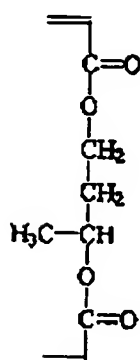
5 <Chemical Formula 1>



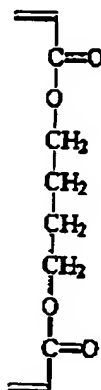
wherein, R' and R'' individually represent hydrogen or methyl; m represents a number from 1 to 10; and R is selected from the group consisting of straight or branched C₁₋₁₀ alkyl, straight or branched C₁₋₁₀ ester, straight or branched C₁₋₁₀ ketone, straight or branched C₁₋₁₀ carboxylic acid, straight or branched C₁₋₁₀ acetal, straight or branched C₁₋₁₀ alkyl including at least one hydroxyl group, straight or branched C₁₋₁₀ ester including at least one hydroxyl group, straight or branched C₁₋₁₀ ketone including at least one hydroxyl group, straight or branched C₁₋₁₀ carboxylic acid including at least one hydroxyl group, and straight or branched C₁₋₁₀ acetal including at least one hydroxyl group.

2. A cross-linking monomer according to claim 1 selected from the group consisting of compounds represented by the following Chemical Formula 2 and Chemical Formula 3:

<Chemical Formula 2>

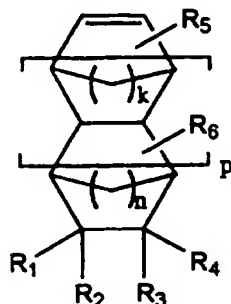


<Chemical Formula 3>



3. A photoresist copolymer comprising the polymerization product of two or more
5 alicyclic olefin derivatives, and a cross-linking monomer according to claim 1.
4. A photoresist copolymer according to claim 3, wherein the alicyclic olefin derivatives comprise compounds represented by the following Chemical Formula 4:

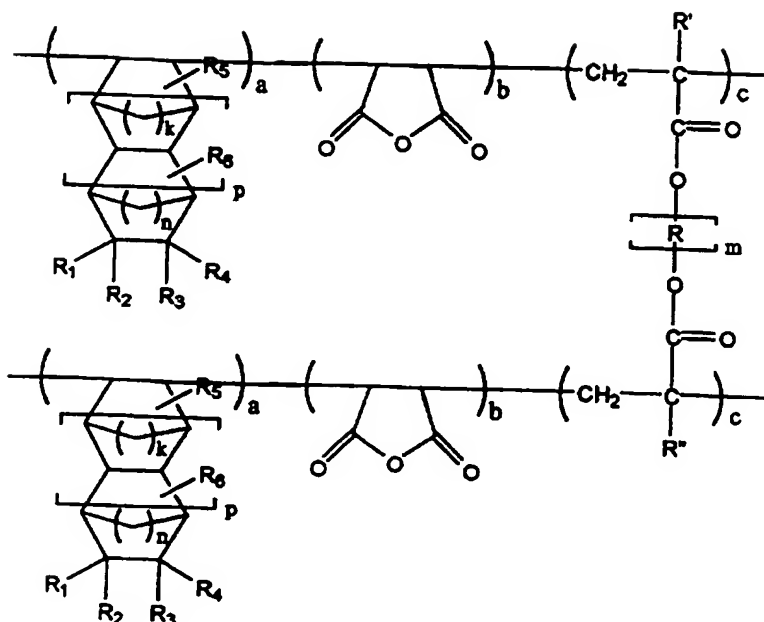
<Chemical Formula 4>



wherein, k and n individually represent the number 1 or 2; p represents a number from 0 to 5, R₅ and R₆ individually represent hydrogen or methyl, R₁, R₂, R₃, and R₄ individually represent hydrogen, straight or branched C₁₋₁₀ alkyl, straight or branched C₁₋₁₀ ester, straight or branched C₁₋₁₀ ketone, straight or branched C₁₋₁₀ carboxylic acid, straight or branched C₁₋₁₀ acetal, straight or branched C₁₋₁₀ alkyl including at least one hydroxyl group, straight or branched C₁₋₁₀ ester including at least one hydroxyl group, straight or branched C₁₋₁₀ ketone including at least one hydroxyl group, straight or branched C₁₋₁₀ carboxylic acid including at least one hydroxyl group, and straight or branched C₁₋₁₀ acetal including at least one hydroxyl group.

5. A photoresist copolymer according to claim 3, wherein said polymerization product further comprises repeating units of maleic anhydride.
6. A photoresist copolymer according to claim 3 represented by the following Chemical Formula 5:

<Chemical Formula 5>



wherein, k and n individually represent the number 1 or 2; m represents a
 number from 1 to 10; p represents a number from 0 to 5; R', R'', R₅ and R₆
 individually represent hydrogen or methyl; R is selected from the group consisting of
 5 straight or branched C₁₋₁₀ alkyl, straight or branched C₁₋₁₀ ester, straight or
 branched C₁₋₁₀ ketone, straight or branched C₁₋₁₀ carboxylic acid, straight or
 branched C₁₋₁₀ acetal, straight or branched C₁₋₁₀ alkyl including at least one
 hydroxyl group, straight or branched C₁₋₁₀ ester including at least one hydroxyl
 group, straight or branched C₁₋₁₀ ketone including at least one hydroxyl group,
 10 straight or branched C₁₋₁₀ carboxylic acid including at least one hydroxyl group,
 and straight or branched C₁₋₁₀ acetal including at least one hydroxyl group; R₁, R₂,
 R₃ and R₄ are individually selected from the group consisting of hydrogen, straight
 or branched C₁₋₁₀ alkyl, straight or branched C₁₋₁₀ ester, straight or branched C₁₋₁₀
 ketone, straight or branched C₁₋₁₀ carboxylic acid, straight or branched C₁₋₁₀
 15 acetal, straight or branched C₁₋₁₀ alkyl including at least one hydroxyl group,
 straight or branched C₁₋₁₀ ester including at least one hydroxyl group, straight or

branched C₁₋₁₀ ketone including at least one hydroxyl group, straight or branched C₁₋₁₀ carboxylic acid including at least one hydroxyl group, and straight or branched C₁₋₁₀ acetal including at least one hydroxyl group; and the ratio a : b : c is 1-50 mol% : 10-50 mol% : 0.1-20 mol%.

- 5 7. A photoresist polymer according to claim 6 comprising poly(maleic anhydride / 2-hydroxyethyl 5-norbornene-2-carboxylate / tert-butyl 5-norbornene-2-carboxylate / 5-norbornene-2-carboxylic acid / 1,3-butanediol diacrylate); or poly(maleic anhydride / 2-hydroxyethyl 5-norbornene-2-carboxylate / tert-butyl 5-norbornene-2-carboxylate / 5-norbornene-2-carboxylic acid / 1,4-butanediol diacrylate).
- 10 8. A process for preparing a photoresist copolymer, which comprises the steps of (a) dissolving two or more photoresist comonomers and a photoresist cross-linking monomer according to claim 1 in organic solvent and (b) adding a polymerization initiator or polymerization catalyst thereto to induce a polymerization reaction.
- 15 9. A process for preparing a photoresist copolymer according to claim 8, wherein step (b) is carried out under an atmosphere of nitrogen or argon.
- 10 10. A process for preparing a photoresist copolymer according to claim 8, wherein step (b) is carried out at a temperature between 60°C and 130°C.
- 20 11. A process for preparing a photoresist copolymer according to claim 8, wherein step (b) is carried out under the pressure between 0.0001 and 5 atm.
- 25 12. A process for preparing a photoresist copolymer according to claim 8, wherein the organic solvent for polymerization is one or more solvent(s) selected from the group consisting of cyclohexanone, methyl ethyl ketone, benzene, toluene, dioxane, tetrahydrofuran, propylene glycol methyl ether acetate and dimethylformamide.
13. A process for preparing a photoresist copolymer according to claim 8, wherein

the polymerization initiator is one or more compound(s) selected from the group consisting of 2,2-azobisisobutyronitrile (AIBN), acetyl peroxide, lauryl peroxide, tert-butyl peracetate, tert-butyl hydroperacetate and tert-butyl peroxide.

- 5 14. A photoresist composition comprising (i) a photoresist copolymer according to claim 3, and (ii) an organic solvent.
15. A photoresist composition according to claim 14, which further comprises a photoacid generator.
- 10 16. A photoresist composition according to claim 15, wherein the photoacid generator is one or more compound(s) selected from the group consisting of diphenyl iodide hexafluorophosphate, diphenyl iodide hexafluoroarsenate, diphenyl iodide hexafluoroantimonate, diphenyl p-methoxyphenyl triflate, diphenyl p-toluenyl triflate, diphenyl p-isobutylphenyl triflate, diphenyl p-tert-butylphenyl triflate, triphenylsulfonium hexafluorophosphate, triphenylsulfonium hexafluoroarsenate, triphenylsulfonium hexafluoroantimonate, triphenylsulfonium triflate, and dibutylnaphtylsulfonium triflate.
- 15 17. A process for forming a photoresist pattern, which comprises the steps of (a) coating a photoresist composition according to claim 14 on a wafer, (b) exposing the wafer to patterned light by employing an exposers, and (c) developing the exposed wafer.
- 20 18. A process for forming a photoresist pattern according to claim 17, wherein the step (b) is carried out by using a light source selected from the group consisting of ArF, KrF, E-beam, X-ray, EUV (extremely ultraviolet) and DUV (deep ultraviolet).
- 25 19. A process according to claim 18, which further comprises baking step(s) before and/or after step (b).

20. A process according to claim 19, wherein the baking step(s) are performed at a temperature of 50°C to 200°C.
21. A process according to claim 17, wherein the developing step (c) is carried out using an aqueous solution of TMAH (tetramethylamine hydroxide).
- 5 22. A semiconductor element manufactured by using a process according to claim 17.



Application No: GB 9929650.1
Claims searched: 1-22

Examiner: Dr William Thomson
Date of search: 20 March 2000

Patents Act 1977
Search Report under Section 17

Databases searched:

UK Patent Office collections, including GB, EP, WO & US patent specifications, in:

UK Cl (Ed.R): C2C (CCJ); C3P (PDY)

Int Cl (Ed.7): C07C 69/602; C08F 22/14

Other: ONLINE: CAS-ONLINE, EPODOC, JAPIO, WPI

Documents considered to be relevant:

Category	Identity of document and relevant passage	Relevant to claims
X	US 5777068 (TANAKA ET AL) See whole document, in particular column 1, lines 19-24, column 13, line 24 - column 15, line 15 and claims 19-24	1 and 3-22
X	US 4329419 (GOFF ET AL) See whole document, in particular Example 3 and claim 4	1 and 3-22

X	Document indicating lack of novelty or inventive step	A	Document indicating technological background and/or state of the art.
Y	Document indicating lack of inventive step if combined with one or more other documents of same category.	P	Document published on or after the declared priority date but before the filing date of this invention.
&	Member of the same patent family	E	Patent document published on or after, but with priority date earlier than, the filing date of this application.